

MA3X199

Silicon epitaxial planar type

For high voltage switching circuit

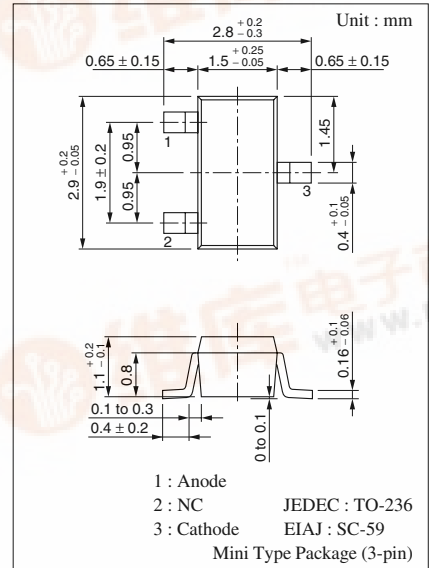
■ Features

- High breakdown voltage: $V_R = 200\text{ V}$
- Short reverse recovery time t_{rr}
- Small package, allowing automatic mounting

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

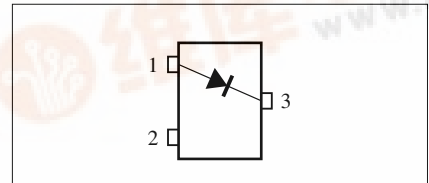
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	200	V
Repetitive peak reverse voltage	V_{RRM}	250	V
Average forward current	$I_{F(AV)}$	100	mA
Repetitive peak forward current	I_{FRM}	225	mA
Non-repetitive peak forward surge current*	I_{FSM}	500	mA
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) * : $t = 1\text{ s}$



Marking Symbol: M3A

Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 200\text{ V}$			1	μA
Forward voltage (DC)	V_F	$I_F = 100\text{ mA}$			1.2	V
Terminal capacitance	C_t	$V_R = 0\text{ V}, f = 1\text{ MHz}$			3	pF
Reverse recovery time*	t_{rr}	$I_F = I_R = 10\text{ mA}$ $I_{rr} = 1\text{ mA}, R_L = 100\ \Omega$			60	ns

Note) 1. Rated input/output frequency: 20 MHz

2. * : t_{rr} measuring circuit

